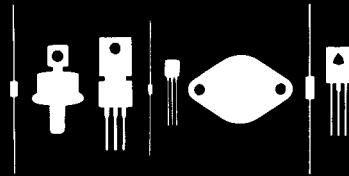


CENTRAL
 SEMICONDUCTOR CORP.
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145 Adams Avenue
 Hauppauge, New York 11788



TIP42
 TIP42A
 TIP42B
 TIP42C

SILICON PNP TRANSISTOR

JEDEC TO-220

DESCRIPTION

The CENTRAL SEMICONDUCTOR TIP42 Series is a PNP Epitaxial-Base Silicon Power Transistor designed for power amplifier and high-speed switching applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>	<u>TIP42</u>	<u>TIP42A</u>	<u>TIP42B</u>	<u>TIP42C</u>	<u>UNIT</u>
Collector-Base Voltage	V_{CBO}	40	60	80	100	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	5.0	5.0	V
Collector-Emitter Voltage	V_{CEO}	40	60	80	100	V
Collector Current, Continuous	I_C	6.0	6.0	6.0	6.0	A
Collector Current, Peak	I_{CM}	10	10	10	10	A
Base Current	I_B	3.0	3.0	3.0	3.0	A
Power Dissipation	P_D	65	65	65	65	W
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	2.0	2.0	2.0	2.0	W
Operating and Storage	T_J, T_{Stg}	-65 to +150		-65 to +150		°C
Junction Temperature						

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNIT</u>
I_{CEO}	$V_{CE}=30\text{V}$ (TIP42, TIP42A)		0.7	mA
I_{CEO}	$V_{CE}=60\text{V}$ (TIP42B, TIP42C)		0.7	mA
I_{CES}	$V_{CE}=\text{Rated } V_{CEO}$		0.4	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		1.0	mA
BV_{CEO}	$I_C=30\text{mA}$, (TIP42)	40		V
BV_{CEO}	$I_C=30\text{mA}$, (TIP42A)	60		V
BV_{CEO}	$I_C=30\text{mA}$, (TIP42B)	80		V
BV_{CEO}	$I_C=30\text{mA}$, (TIP42C)	100		V
$V_{CE(SAT)}$	$I_C=6.0\text{A}$, $I_B=0.6\text{A}$		1.5	V
$V_{BE(on)}$	$V_{CE}=4.0\text{V}$, $I_C=6.0\text{A}$		2.0	V
hFE	$V_{CE}=4.0\text{V}$, $I_C=0.3\text{A}$	30		-
hFE	$V_{CE}=4.0\text{V}$, $I_C=3.0\text{A}$	15	75	-
hfe	$V_{CE}=10\text{V}$, $I_C=0.5\text{A}$, $f=1\text{ kHz}$	20		-
f_T	$V_{CE}=10\text{V}$, $I_C=0.5\text{A}$, $f=1\text{ MHz}$	3		MHz
t_{on}	$I_C=6.0\text{A}$, $I_{B1}=I_{B2}=0.6\text{A}$, $R_L=5.0\text{ OHMS}$	0.4	TYP	μSEC
t_{off}	$I_C=6.0\text{A}$, $I_{B1}=I_{B2}=0.6\text{A}$, $R_L=5.0\text{ OHMS}$	0.7	TYP	μSEC